



SEMITRANS® 4

SKM600GA12V

Features

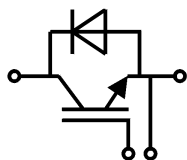
- V-IGBT = 6. Generation Trench V-IGBT (Fuji)
- CAL4 = Soft switching 4. Generation CAL-diode
- Isolated copper baseplate using DBC technology (Direct Copper Bonding)
- UL recognized, file no. E63532
- Increased power cycling capability
- With integrated gate resistor
- Low switching losses at high di/dt

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders
- Switched reluctance motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$



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Absolute Maximum Ratings

Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	908
		$T_c = 80^\circ\text{C}$	692
I_{Cnom}		600	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	1800	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 720\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 125^\circ\text{C}$	10
T_j		-40 ... 175	$^\circ\text{C}$
Inverse diode			
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	707
		$T_c = 80^\circ\text{C}$	529
I_{Fnom}		600	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$	1800	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	3240	A
T_j		-40 ... 175	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$	500	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V

Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 600\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.75	2.20	V
		$T_j = 150^\circ\text{C}$	2.20	2.50	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	0.94	1.04	V
		$T_j = 150^\circ\text{C}$	0.88	0.98	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.35	1.93	m Ω
		$T_j = 150^\circ\text{C}$	2.20	2.53	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 24\text{ mA}$	5.5	6	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	36		nF
C_{oes}		$f = 1\text{ MHz}$	3.55		nF
C_{res}		$f = 1\text{ MHz}$	3.536		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		6620		nC
R_{Gint}			1.25		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	710		ns
t_r	$I_C = 600\text{ A}$ $V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	85		ns
		$T_j = 150^\circ\text{C}$	76		mJ
E_{on}	$R_{G on} = 2.5\text{ }\Omega$	$T_j = 150^\circ\text{C}$	930		ns
$t_{d(off)}$	$R_{G off} = 2.5\text{ }\Omega$	$T_j = 150^\circ\text{C}$	98		ns
t_f	$di/dt_{on} = 9000\text{ A}/\mu\text{s}$ $di/dt_{off} = 6000\text{ A}/\mu\text{s}$ $du/dt_{off} = 6400\text{ V}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	76		mJ
		$T_j = 150^\circ\text{C}$			
$R_{th(j-c)}$	per IGBT			0.049	K/W



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Typical Applications*

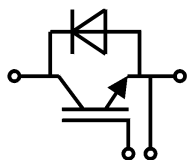
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Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 600\text{ A}$	$T_j = 25^\circ\text{C}$		2.14	2.46	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.07	2.38	V
	chipllevel					
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
	chipllevel	$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		1.4	1.6	m Ω
	chipllevel	$T_j = 150^\circ\text{C}$		1.9	2.1	m Ω
I_{RRM}	$I_F = 600\text{ A}$	$T_j = 150^\circ\text{C}$		635		A
Q_{rr}	$di/dt_{off} = 8600\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		118		μC
E_{rr}	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		43		mJ
	$V_{CC} = 600\text{ V}$					
$R_{th(j-c)}$	per diode				0.086	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.18		m Ω
		$T_c = 125^\circ\text{C}$		0.22		m Ω
$R_{th(c-s)}$	per module			0.02	0.038	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals	M6	2.5		5	Nm
		M4	1.1		2	Nm
w					330	g



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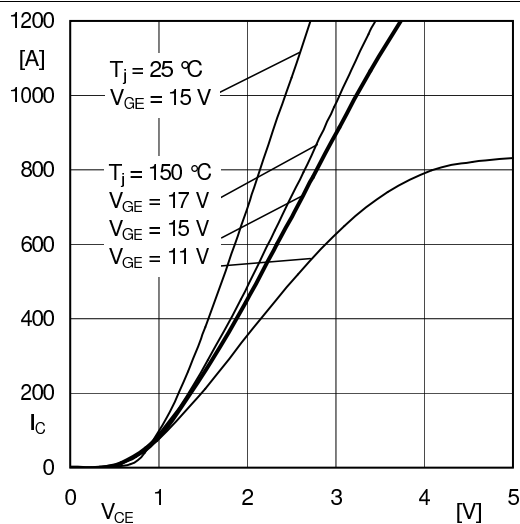


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$

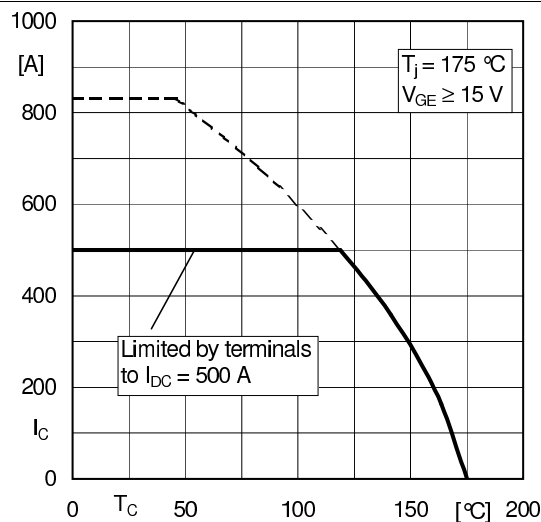


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

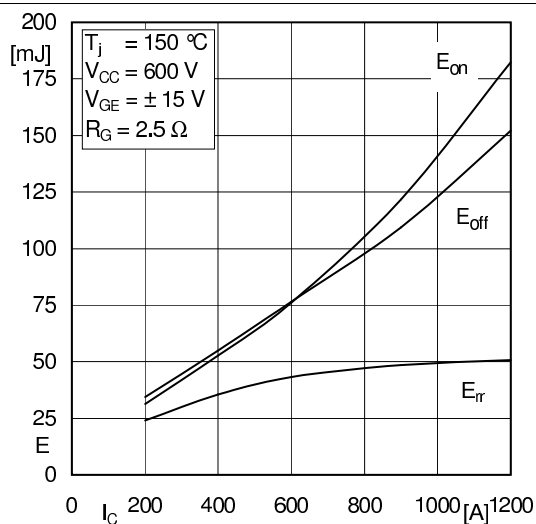


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

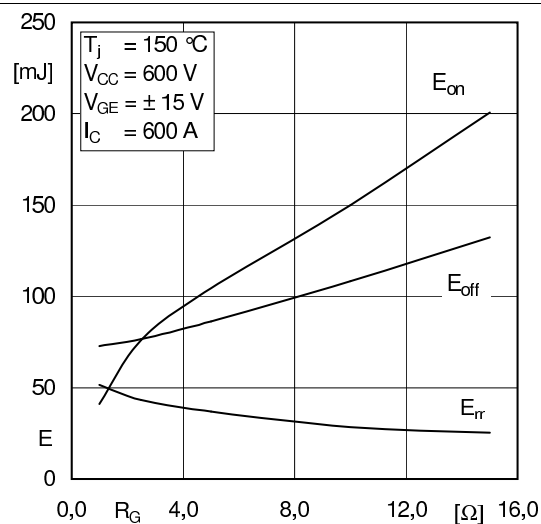


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

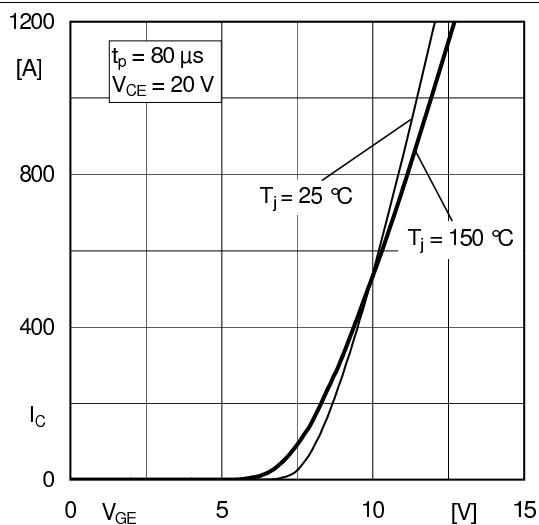


Fig. 5: Typ. transfer characteristic

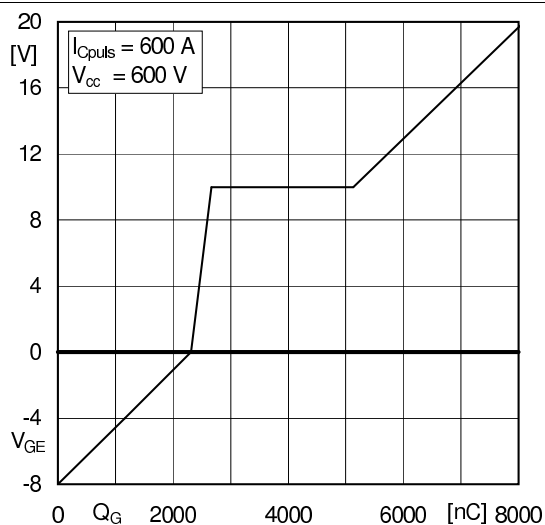
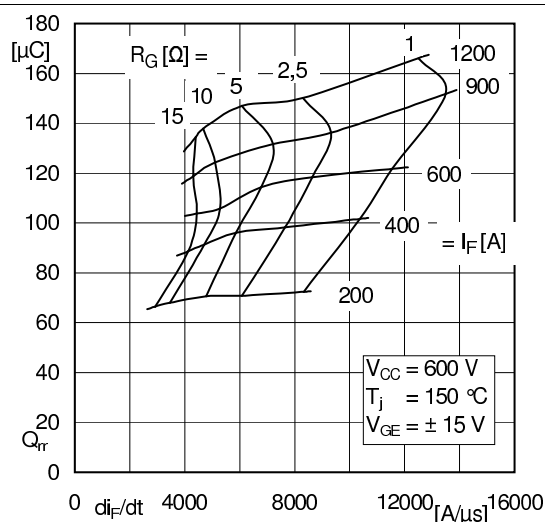
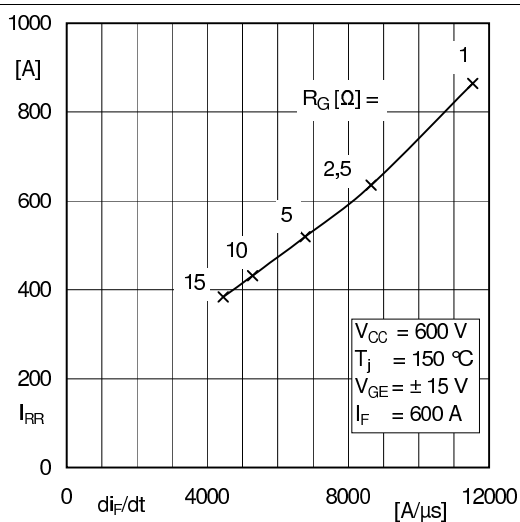
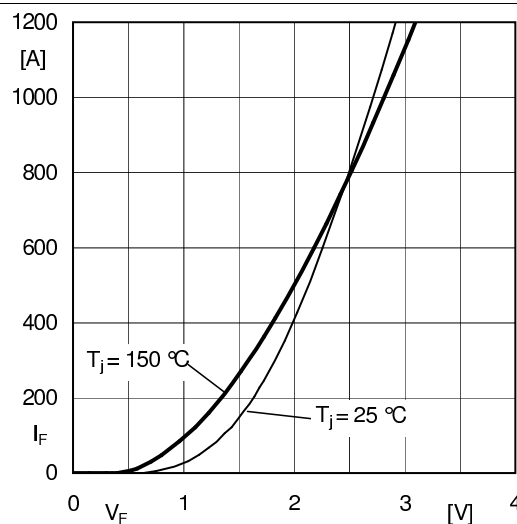
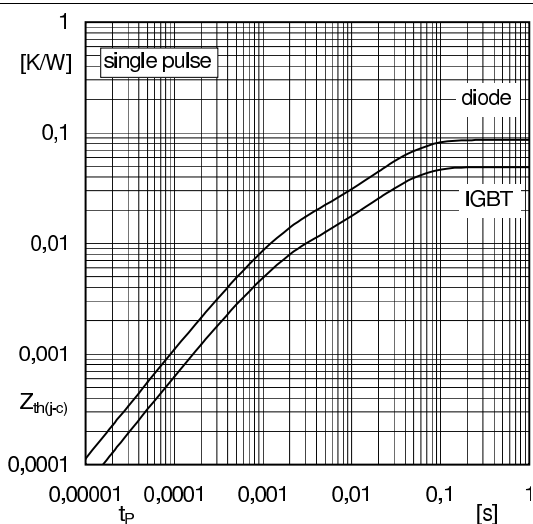
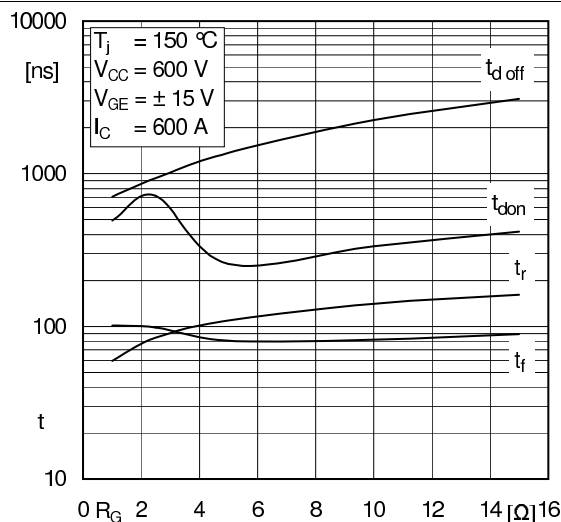
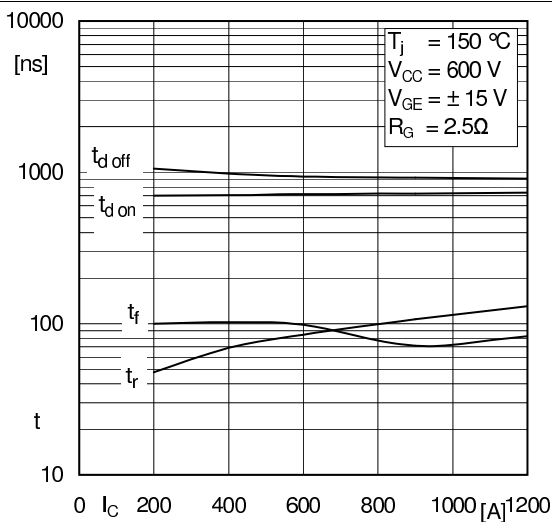
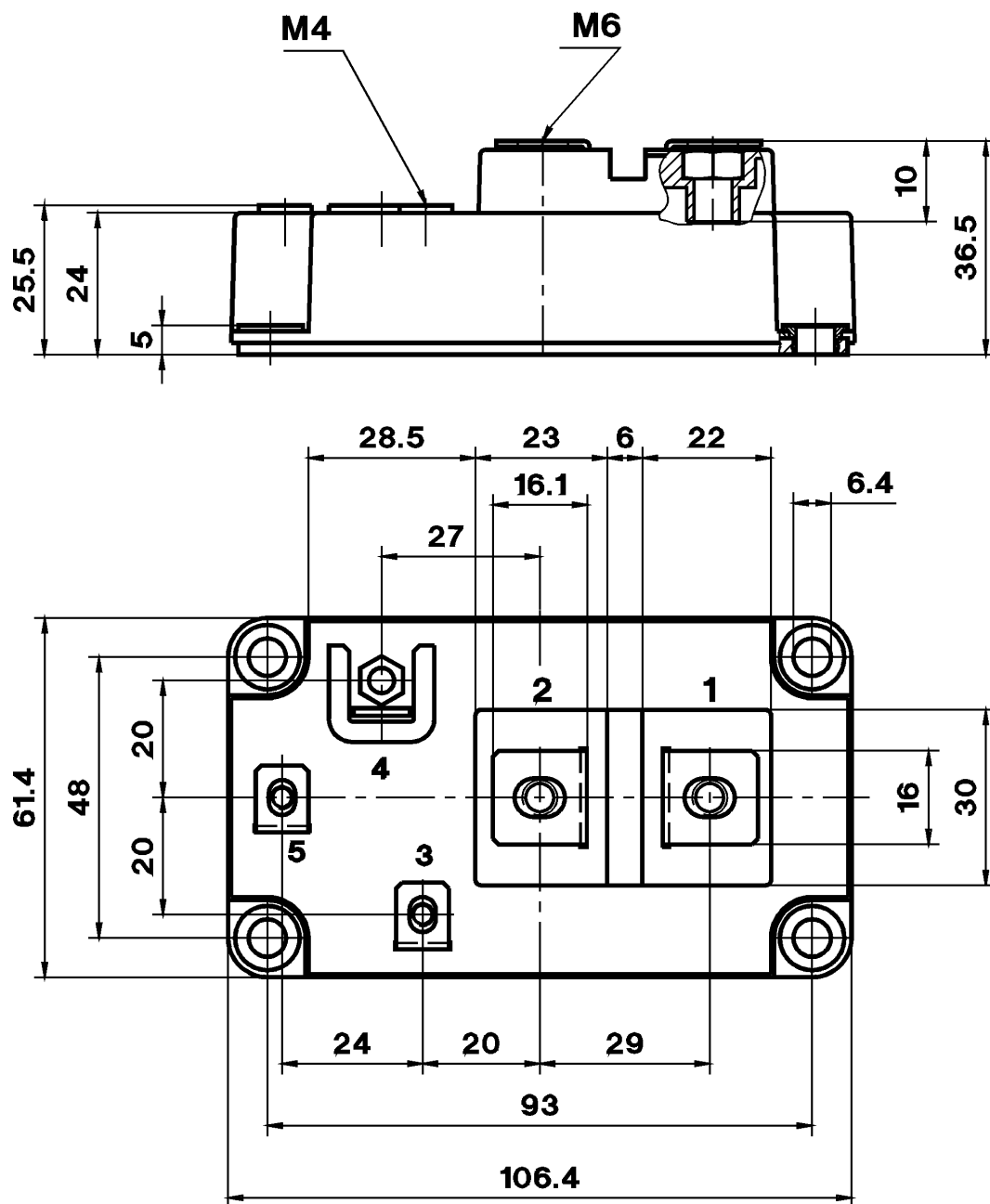
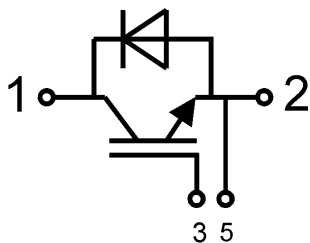


Fig. 6: Typ. gate charge characteristic





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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.